

The documentation and process conversion measures necessary to comply with this revision shall be completed by 20 December 2007.

INCH-POUND

MIL-PRF-19500/114G
20 September 2007
SUPERSEDING
MIL-PR-19500/114F
21 August 1999

PERFORMANCE SPECIFICATION SHEET

SEMICONDUCTOR DEVICE, DIODE, SILICON, VOLTAGE REGULATOR B AND RB TYPES,
IN2804 THROUGH 1N2811, 1N2813, 1N2814, 1N2816, 1N2818 THROUGH
1N2820, 1N2822 THROUGH 1N2827, 1N2829, 1N2831 THROUGH 1N2838, 1N2840 THROUGH 1N2846,
1N4557 THROUGH 1N4562, JAN, JANTX, JANTXV, and JANS

This specification is approved for use by all Departments
and Agencies of the Department of Defense.

* The requirements for acquiring the product described herein shall consist of
this specification sheet and MIL-PRF-19500.

1. SCOPE

1.1 Scope. The specification covers the performance requirements for 50 watt, silicon voltage regulator diodes: B type (standard polarity); RB type (reverse polarity). Four levels of product assurance are provided for each device type as specified in MIL-PRF-19500.

1.2 Physical dimensions. See figure 1 (TO-3).

1.3 Maximum ratings. Maximum ratings are as shown in columns 4, 8, and 10 of the Characteristics and Ratings table herein and as follows:

- a. $P_T = 50 \text{ W}$ at $T_C \geq +75^\circ\text{C}$, Derate at $0.5 \text{ W}/^\circ\text{C}$ above $T_C \geq +75^\circ\text{C}$.
- b. $-65^\circ\text{C} \leq T_{op} \leq 175^\circ\text{C}$; $-65^\circ\text{C} \leq T_{STG} \leq 200^\circ\text{C}$.

1.4 Primary electrical characteristics. Primary electrical characteristics are as shown in columns 2, 9, 12, and 13 of the Characteristics and Ratings table and as follows: Thermal resistance ($R_{\theta JC}$): $2.0^\circ\text{C}/\text{W}$ maximum.

Comments, suggestions, or questions on this document should be addressed to Defense Supply Center, Columbus, ATTN: DSCC-VAC, P.O. Box 3990, Columbus, OH 43218-3990, or emailed to Semiconductor@dsc.dla.mil. Since contact information can change, you may want to verify the currency of this address information using the ASSIST Online database at <http://assist.daps.dla.mil>.

2. APPLICABLE DOCUMENTS.

* 2.1 General. The documents listed in this section are specified in sections 3, 4, or 5 of this specification. This section does not include documents cited in other sections of this specification or recommended for additional information or as examples. While every effort has been made to ensure the completeness of this list, document users are cautioned that they must meet all specified requirements of documents cited in sections 3, 4, or 5 of this specification, whether or not they are listed.

* 2.2 Government documents.

* 2.2.1 Specifications, standards, and handbooks. The following specifications, standards, and handbooks form a part of this document to the extent specified herein. Unless otherwise specified, the issues of these documents are those cited in the solicitation or contract.

DEPARTMENT OF DEFENSE SPECIFICATIONS

MIL-PRF-19500 - Semiconductor Devices, General Specification for.

DEPARTMENT OF DEFENSE STANDARDS

MIL-STD-750 - Test Methods for Semiconductor Devices.

* (Copies of these documents are available online at <http://assist.daps.dla.mil/quicksearch/> or <http://assist.daps.dla.mil>. or from the Standardization Document Order Desk, 700 Robbins Avenue, Building 4D, Philadelphia, PA 19111-5094.)

2.3 Order of precedence. In the event of a conflict between the text of this document and the references cited herein, the text of this document takes precedence. Nothing in this document, however, supersedes applicable laws and regulations unless a specific exemption has been obtained.

3. REQUIREMENTS

* 3.1 General. The individual item requirements shall be as specified in MIL-PRF-19500 and as modified herein.

* 3.2 Qualification. Devices furnished under this specification shall be products that are manufactured by a manufacturer authorized by the qualifying activity for listing on the applicable qualified manufacturer's list (QML) before contract award (see 4.2 and 6.3).

3.3 Abbreviations, symbols, and definitions. Abbreviations, symbols, and definitions used herein shall be as specified in MIL-PRF-19500.

3.4 Interface and physical dimensions. The interface and physical dimensions shall be as specified in MIL-PRF-19500 and herein. Current density of internal conductors shall be as specified in MIL-PRF-19500.

3.4.1 Polarity. Standard units (B) shall have the anode connected to the base. The two pins shall be connected internally. Reversed units (RB) shall have the cathode connected to the base.

3.4.2 Lead finish. Lead finish shall be solderable in accordance with MIL-PRF-19500, MIL-STD-750 and herein. Where a choice of lead finish is desired, it shall be specified in the contract or purchase order (see 6.2).

3.4.3 RB types. Reversed (cathode to base) units shall be marked with an "R" preceding the "B" in the type designation and with a contrasting dot on the base plate.

3.5 Marking. Marking shall be in accordance with MIL-PRF-19500.

3.6 Electrical performance characteristics. Unless otherwise specified herein, the electrical performance characteristics are as specified in 1.3, 1.4, and table I herein.

3.7 Electrical test requirements. The electrical test requirements shall be the subgroups specified in table I herein.

* 3.8 Workmanship. Semiconductor devices shall be processed in such a manner as to be uniform in quality and shall be free from other defects that will affect life, serviceability, or appearance.

4. VERIFICATION

4.1 Classification of Inspections. The inspection requirements specified herein are classified as follows:

- a. Qualification inspection (see 4.2).
- b. Screening (see 4.3)
- c. Conformance inspection (see 4.4, and tables I, II, and III).

4.1.1 Sampling and inspection. Sampling and inspection shall be in accordance with MIL-PRF-19500, and as specified herein. Lot accumulation period shall be 6 months in lieu of 6 weeks.

4.2 Qualification inspection. Qualification inspection shall be in accordance with MIL-PRF-19500.

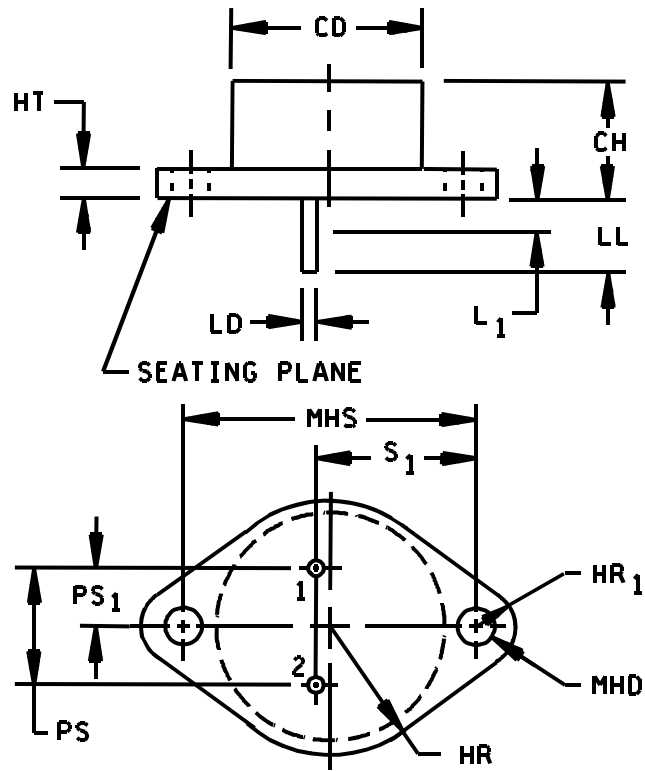


FIGURE 1. Physical dimensions (similar to TO-3).

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Ltr	Dimensions				Notes
	Inches		Millimeters		
	Min	Max	Min	Max	
CH	.270	.380	6.86	9.65	
LD	.048	.053	0.97	1.35	
CD		.875		22.23	
PS	.420	.440	10.67	11.18	3
PS ₁	.205	.225	5.21	5.72	3
HT	.060	.135	1.52	3.43	
LL	.312	.500	7.92	12.70	
L ₁		.050		1.27	
MHD	.151	.165	3.84	4.09	
MHS	1.177	1.197	29.90	30.40	
HR	.495	.525	12.57	13.34	
HR ₁	.131	.188	3.33	4.78	
S ₁	.655	.675	16.64	17.15	

NOTES:

1. Dimensions are in inches.
2. Millimeter equivalents are given for general information only.
3. These dimensions should be measured at points .050 inch (1.27 mm) +.005 inch (0.13 mm) -.000 inch (0.00 mm) below seating plane.
4. The seating plane of the header shall be flat within .001 inch (0.03 mm) concave to .004 inch (0.10 mm) convex .001 inch (0.03 mm) concave to .006 inch (0.15 mm) convex overall.
5. Pins 1 and 2 are internally connected with an internal jumper.
6. Devices with B suffix have the anode internally connected to the case and devices with RB suffix (reverse polarity) have the cathode internally connected to the case.
7. In accordance with ASME Y14.5M, diameters are equivalent to ϕ x symbology.

FIGURE 1. Physical dimensions (similar to TO-3) - Continued.

* 4.3 Screening (JANS, JANTXV, and JANTX levels only). Screening shall be in accordance with appendix E, table E-IV of MIL-PRF-19500, and as specified herein. The following measurements shall be made in accordance with table I herein. Devices that exceed the limits of table I herein shall not be acceptable.

Screen (see appendix E, table E-IV of MIL-PRF-19500)	Measurement	
	JANS level	JANTX and JANTXV levels
9	I_{R1} and V_Z (for devices with V_Z (NOM) \geq 10 V dc; see column 2 of table III).	Not applicable
11	I_{R1} and V_Z ; ΔI_{R1} = 100 percent of initial value or 2 μ A dc, whichever is greater; ΔV_Z = ± 1 percent of initial value (for devices with V_Z (NOM) \geq 10 V dc; see column 2 of table III).	I_{R1} and V_Z
12	See 4.3.1	See 4.3.1
13	Subgroup 2 (except forward voltage test) and subgroup 3 of table I herein; ΔI_{R1} = 100 percent of initial value or 2 μ A dc, whichever is greater, ΔV_Z = ± 1 percent of initial value.	Subgroup 2 (except forward voltage test) of table I herein; ΔI_{R1} = 100 percent of initial value or 2 μ A dc, whichever is greater, ΔV_Z = ± 1 percent of initial value.

4.3.1 Power burn-in conditions. Power burn-in conditions are as follows: I_Z : Column 14 of table III at $T_C = 150^\circ\text{C}$.

4.4 Conformance inspection. Conformance inspection shall be in accordance with MIL-PRF-19500 and as specified herein. Group A inspection shall be performed on each subplot.

4.4.1 Group A inspection. Group A inspection shall be conducted in accordance with MIL-PRF-19500, and table I herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein.

* 4.4.2 Group B inspection. Group B inspection shall be conducted in accordance with the tests and conditions specified for subgroup testing in appendix E, table E-VIa (JANS) and table E-VIb (JAN, JANTX, and JANTXV) of MIL-PRF-19500 and herein. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein. Delta measurements shall be in accordance with table II herein.

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4.4.2.1 Group B inspection, appendix E, table E-VIa (JANS) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B4	1037	I_z = column 8 of table III; $T_C = 30 \pm 3^\circ\text{C}$; $t_{on} = t_{off} = 3$ minutes minimum for 2,000 cycles.
B5	1027	I_z = column 14 of table III for 96 hours; $T_A = 125^\circ\text{C}$ or adjusted, as required, to give an average lot; $T_J = 275^\circ\text{C}$.
B6	4081	$R_{\theta JC} = 2.0^\circ\text{C/W}$ maximum $T_C = 30 \pm 3^\circ\text{C}$. For purposes of this test "junction to case" shall be used in lieu of "junction to lead" and $R_{\theta JC}$ shall be used in lieu of $R_{\theta JL}$. The case shall be the reference point for calculation of junction to case thermal resistance ($R_{\theta JC}$). The mounting arrangement shall be with heat sink to case.

* 4.4.2.2 Group B inspection, appendix E, table E-VIb (JAN, JANTX and JANTXV) of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>
B2	4066	I_{ZSM} = column 10 of table III.
B3	1027	$T_C = 150^\circ\text{C}$; I_z = column 14 of table III.
B5	4081	$R_{\theta JC} = 2.0^\circ\text{C/W}$ maximum $T_C = 30 \pm 3^\circ\text{C}$ For purposes of this test "junction to case" shall be used in lieu of "junction to lead" and $R_{\theta JC}$ shall be used in lieu of $R_{\theta JL}$. The case shall be the reference point for calculation of junction to case thermal resistance ($R_{\theta JC}$). The mounting arrangement shall be with heat sink to case.

* 4.4.3 Group C inspection. Group C inspection shall be conducted in accordance with the conditions specified for subgroup testing in appendix E, table E-VII of MIL-PRF-19500 and as follows. Electrical measurements (end-points) shall be in accordance with table I, subgroup 2 herein. Delta measurements shall be in accordance with table II herein.

4.4.3.1 Group C inspection, appendix E, table E-VII of MIL-PRF-19500.

<u>Subgroup</u>	<u>Method</u>	<u>Condition</u>	<u>Max limits</u>	<u>Unit</u>
C5		Not applicable.		
C6	1026	$T_C = 150^\circ\text{C}$; I_z = column 14 of table III.		
C8	4071	α_{VZ} JAN, JANTX, and JANTXV levels only I_z = column 5 of table V; $T_1 = 30 \pm 3^\circ\text{C}$, $T_2 = T_1 + 100^\circ\text{C}$ each subplot. $n = 22, c = 0$	Col. 13 of table III	%/ $^\circ\text{C}$
C9		Voltage regulation (see 4.5.2), each subplot. $n = 22, c = 0$	Col. 9 of table III	V dc

4.5 Methods of inspection. Methods of inspection shall be as specified in the appropriate tables and as follows.

4.5.1 Surge current I_{ZSM} . The currents specified in column 10 of table III shall be applied in the reverse direction and shall be superimposed on the current (I_Z = column 5 of table III) a total of five surges at 1 minute intervals. Each individual surge shall be a one-half square wave pulse of 1/120 second duration or a one-half sine wave with the same effective (rms) current.

4.5.2 Voltage regulation $V_{Z(reg)}$. A current at 10 percent of I_Z (column 8 of table III herein) shall be maintained until thermal equilibrium is obtained and the V_Z shall be noted. The current shall then be increased to a level of 50 percent of I_Z (column 8 of table III herein) and maintained at this level until thermal equilibrium is obtained, at which time the voltage change shall not exceed column 9 of table III. During this test, the case temperature (T_C) of the diode shall be equal to $30 \pm 3^\circ\text{C}$.

4.5.3 Regulator voltage. The test current (column 5 of table III) shall be applied until thermal equilibrium is obtained. During this test, the case temperature (T_C) of the diode shall be equal to $30 \pm 3^\circ\text{C}$.

4.5.4 Temperature coefficient of regulator voltage (αV_Z). The device shall be temperature stabilized with current applied prior to reading regulator voltage at the specified case temperatures.

4.5.5 Inspection condition. Unless otherwise specified herein, all inspections shall be made at case temperature (T_C) of $30 \pm 3^\circ\text{C}$

4.5.6 Test ratings. Test ratings shall be as shown in table III. Type numbers with the suffix "RB" shall have identical requirements as shown in table III for the corresponding B type except the polarity shall be as specified in 3.4.1 herein.

4.5.7 Reverse current. The specified reverse voltage shall be applied to pin 1 and pin 2 separately and the reverse current measured at each pin.

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TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits <u>2/</u>		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 1</u>						
Visual and mechanical inspection	2071					
<u>Subgroup 2</u>						
Forward voltage	4011	$I_F = 10 \text{ A dc}$	V_F		1.5	V dc
Reverse current	4016	$V_R =$ column 11 of table III; DC method (see 4.5.7)	I_{R1}		Col. 12	$\mu\text{A dc}$
Regulator voltage	4022	$I_Z =$ column 5 of table III	V_Z	Col. 3	Col. 4	V dc
<u>Subgroup 3</u>						
High temperature operation:		$T_A = 150^\circ\text{C}$				
Reverse current	4016	$V_R =$ column 11 of table III; DC method	I_{R2}		Col. 15	$\mu\text{A dc}$
<u>Subgroup 4</u>						
Small-signal breakdown impedance	4051	$I_Z =$ column 5 of table III; $I_{sig} = 10$ percent of I_Z	Z_Z		Col. 6	ohms
Knee impedance	4051	$I_{ZK} = 5 \text{ mA dc};$ $I_{sig} = 10$ percent of I_Z	Z_{ZK}		Col. 7	ohms
<u>Subgroup 5</u>						
Not applicable						
<u>Subgroup 6</u>						
Surge current (see 4.5.1)	4066	$I_{ZSM} =$ column 10 of table III				
End point electrical measurements		See table I, subgroup 2 herein				
<u>Subgroup 7</u>						
Not applicable						

See footnotes at end of table.

TABLE I. Group A inspection.

Inspection <u>1/</u>	MIL-STD-750		Symbol	Limits <u>2/</u>		Unit
	Method	Conditions		Min	Max	
<u>Subgroup 8</u>		JANS level only n = 22, c = 0				
Voltage regulation (see 4.5.2)			$V_{Z(\text{reg})}$		Col. 9	V dc
Temperature coefficient of regulator voltage (see 4.5.4)	4071	$I_Z = \text{column 5 of table III};$ $T_1 = 30 \pm 3^\circ\text{C}, T_2 = T_1 + 100^\circ\text{C}$	α_{VZ}		Col. 13	%/ $^\circ\text{C}$

1/ For JANS, all devices required by the specified sampling plan shall be subjected to subgroups 2, 3, and 4 combined.

2/ Column references are for table III herein.

TABLE II. Groups A, B and C delta electrical measurements. 1/ 2/

Step	Inspection	MIL-STD-750		Symbol	Limits		Unit
		Method	Conditions		Min	Max	
1.	Forward voltage	4011	$I_F = 10 \text{ A dc}$	ΔV_F 3/			$\pm 50 \text{ mV dc}$ change from previously measured value.

1/ The delta electrical measurements for appendix E, table E-VIa (JANS) of MIL-PRF-19500 are as follows:

- a. Subgroup 3, see table II herein, step 1.
- b. Subgroup 4, see table II herein, step 1.
- c. Subgroup 5, see table II herein, step 1.

2/ The delta electrical measurements for appendix E, table E-VII of MIL-PRF-19500 are as follows:

- a. Subgroup 2, see table II herein, step 1 (JANS).
- b. Subgroup 3, see table II herein, step 1 (JANS).
- c. Subgroup 6, see table II herein, step 1.

3/ Devices which exceed the group A limits for this test shall not be accepted.

TABLE III. Characteristics and ratings.

Col 1	Col 2	Col 3	Col 4	Col 5	Col 6	Col 7	Col 8	Col 9	Col 10	Col 11	Col 12	Col 13	Col 14	Col 15
Voltage group (see 4.5.6)	V _Z Nom	V _Z Min	V _Z Max	I _Z Test current T _C = 30°C	Z _Z Impedance	Z _{ZK} Knee impedance	I _Z Max dc current T _C = 30°C	V _{Z(reg)} Voltage regulation	I _{ZSM} T _C = 30°C	V _R Reverse voltage	I _{R1} Reverse current dc	α _{VZ} Temperature coefficient	I _Z Max dc current T _C = 150°C	I _{R2} Reverse current T _A = 150°C
	volts	volts	volts	mA dc	ohms	ohms	mA dc	volts	A dc	volts	μA dc	%/°C	mA dc	μA dc
1N4557B, RB	3.9	3.70	4.09	3,200	0.16	400	10,000	0.66	40.0	0.5	150	-.050	3,200	1/
1N4558B, RB	4.3	4.08	4.51	2,900	0.16	500	9,000	0.58	38.0	0.5	150	-.035	2,950	
1N4559B, RB	4.7	4.46	4.93	2,650	0.12	600	8,000	0.40	35.0	1.0	100	± .015	2,650	
1N4560B, RB	5.1	4.84	5.35	2,450	0.12	650	7,500	0.36	32.0	1.0	20	.035	2,450	
1N4561B, RB	5.6	5.32	5.88	2,250	0.12	900	7,000	0.34	30.0	1.0	20	.050	2,250	
1N4562B, RB	6.2	5.89	6.51	2,000	0.14	1,000	6,500	0.36	25.0	2.0	20	.055	2,000	1/
1N2804B, RB	6.8	6.46	7.14	1,850	0.2	70	7,000	0.4	37.0	4.5	150	.057	1,850	1,000
1N2805B, RB	7.5	7.13	7.87	1,700	0.3	70	6,360	0.5	33.0	5.0	100	.067	1,700	750
1N2806B, RB	8.2	7.79	8.61	1,500	0.4	70	5,800	0.6	29.0	5.4	50	.070	1,500	500
1N2807B, RB	9.1	8.65	9.55	1,370	0.5	70	5,240	0.7	26.5	6.1	25	.075	1,370	400
1N2808B, RB	10	9.50	10.50	1,200	0.6	80	4,760	0.9	24.0	6.7	25	.081	1,200	300
1N2809B, RB	11	10.45	11.55	1,100	0.8	80	4,330	1.0	21.5	8.4	10	.085	1,100	200
1N2810B, RB	12	11.40	12.60	1,000	1.0	80	3,970	1.1	20.0	9.1	10	.079	1,000	200
1N2811B, RB	13	12.35	13.65	960	1.1	80	3,750	1.2	18.5	9.9	10	.080	960	200
1N2813B, RB	15	14.25	15.75	830	1.4	80	3,170	1.5	15.5	11.4	10	.082	830	200
1N2814B, RB	16	15.20	16.80	780	1.6	80	2,970	1.6	14.75	12.2	10	.083	780	200
1N2816B, RB	18	17.10	18.90	700	2.0	80	2,640	1.9	12.75	13.7	10	.085	700	200
1N2818B, RB	20	19.00	21.00	630	2.4	80	2,380	2.3	11.75	15.2	10	.086	630	200
1N2819B, RB	22	20.90	23.10	570	2.5	80	2,160	2.5	10.5	16.7	10	.087	570	200
1N2820B, RB	24	22.80	25.20	520	2.6	80	1,980	2.6	9.75	18.2	10	.088	520	200
1N2822B, RB	27	25.65	28.35	460	2.8	90	1,760	2.9	8.25	20.6	10	.090	460	200
1N2823B, RB	30	28.50	31.50	420	3.0	90	1,590	3.0	7.75	22.8	10	.091	420	200
1N2824B, RB	33	31.35	34.65	380	3.2	90	1,440	3.2	7.25	25.1	10	.092	380	200
1N2825B, RB	36	34.20	37.80	350	3.5	90	1,320	3.4	6.5	27.4	10	.093	350	200
1N2826B, RB	39	37.10	40.90	320	4.0	90	1,220	3.6	5.88	29.7	10	.094	320	200

See footnotes at end of table.

TABLE III. Characteristics and ratings - Continued.

Col 1	Col 2	Col 3	Col 4	Col 5	Col 6	Col 7	Col 8	Col 9	Col 10	Col 11	Col 12	Col 13	Col 14	Col 15
Voltage group (see 4.5.6)	V _Z Nom	V _Z Min	V _Z Max	I _Z Test current T _C = 30°C	Z _Z Impedance	Z _{ZK} Knee impedance	I _Z Max dc current T _C = 30°C	V _{Z(reg)} Voltage regulation	I _{ZSM} T _C = 30°C	V _R Reverse voltage	I _{R1} Reverse current dc	α _{VZ} Temperature coefficient	I _Z Max dc current T _C = 150°C	I _{R2} Reverse current T _A = 150°C
	volts	volts	volts	mA dc	ohms	ohms	mA dc	volts	A dc	volts	μA dc	%/°C	mA dc	μA dc
1N2827B, RB	43	40.90	45.10	290	4.5	90	1,110	3.8	5.38	32.7	10	.095	290	200
1N2829B, RB	47	44.65	49.35	270	5.0	100	1,020	4.0	4.90	35.8	10	.095	270	200
1N2831B, RB	51	48.45	53.55	245	5.2	100	930	4.4	4.63	38.8	10	.096	245	200
1N2832B, RB	56	53.20	58.80	220	6.0	110	850	4.75	4.13	42.6	10	.096	220	200
1N2833B, RB	62	58.90	65.10	200	7.0	120	770	5.0	3.68	47.1	10	.097	200	200
1N2834B, RB	68	64.60	71.40	180	8	140	700	5.5	3.35	51.7	10	.097	180	200
1N2835B, RB	75	71.25	78.75	170	9	150	640	5.75	3.00	56.0	10	.098	170	200
1N2836B, RB	82	77.90	86.10	150	11	160	580	6.25	2.75	62.2	10	.098	150	200
1N2837B, RB	91	86.45	95.55	140	15	180	530	6.75	2.35	69.2	10	.099	140	200
1N2838B, RB	100	95.0	105.0	120	20	200	480	7.5	2.25	76.0	10	.100	120	200
1N2840B, RB	110	104.5	115.5	110	30	220	430	9.0	2.05	83.6	10	.100	110	200
1N2841B, RB	120	114.0	126.0	100	40	240	400	9.5	1.88	91.2	10	.100	100	200
1N2842B, RB	130	123.5	136.5	95	50	275	370	10.0	1.73	98.8	10	.100	95	200
1N2843B, RB	150	142.5	157.5	85	75	400	320	12.0	1.50	114.0	10	.100	85	200
1N2844B, RB	160	152.0	168.0	80	80	450	300	13.0	1.43	121.6	10	.100	80	200
1N2845B, RB	180	171.0	189.0	68	90	525	260	14.5	1.25	136.8	10	.100	68	200
1N2846B, RB	200	190.0	210.0	65	100	600	240	16.0	1.10	152.0	10	.100	65	200

1/ This test is not applicable for devices 1N4557B, RB through 1N4562B, RB

PACKAGING

* 5.1 Packaging. For acquisition purposes, the packaging requirements shall be as specified in the contract or order (see 6.2). When packaging of materiel is to be performed by DoD or in-house contractor personnel, these personnel need to contact the responsible packaging activity to ascertain packaging requirements. Packaging requirements are maintained by the Inventory Control Point's packaging activities within the Military Service or Defense Agency, or within the Military Service's system commands. Packaging data retrieval is available from the managing Military Department's or Defense Agency's automated packaging files, CD-ROM products, or by contacting the responsible packaging activity.

6. NOTES

* (This section contains information of a general or explanatory nature that may be helpful, but is not mandatory. The notes specified in MIL-PRF-19500 are applicable to this specification.)

* 6.1 Intended use. Semiconductors conforming to this specification are intended for original equipment design applications and logistic support of existing equipment.

6.2 Acquisition requirements. Acquisition documents should specify the following:

- a. Title, number, and date of this specification.
- b. Packaging requirements (see 5.1).
- c. Lead finish (see 3.4.2).
- d. Product assurance level and type designator.

* 6.3 Qualification. With respect to products requiring qualification, awards will be made only for products which are, at the time of award of contract, qualified for inclusion in Qualified Manufacturers List (QML 19500) whether or not such products have actually been so listed by that date. The attention of the contractors is called to these requirements, and manufacturers are urged to arrange to have the products that they propose to offer to the Federal Government tested for qualification in order that they may be eligible to be awarded contracts or orders for the products covered by this specification. Information pertaining to qualification of products may be obtained from Defense Supply Center, Columbus, ATTN: DSCC/VQE, P.O. Box 3990, Columbus, OH 43218-3990 or e-mail vqe.chief@dla.mil.

* 6.4 Changes from previous issue. The margins of this specification are marked with asterisks to indicate where changes from the previous issue were made. This was done as a convenience only and the Government assumes no liability whatsoever for any inaccuracies in these notations. Bidders and contractors are cautioned to evaluate the requirements of this document based on the entire content irrespective of the marginal notations and relationship to the last previous issue.

Custodians:
Army – CR
Navy – EC
Air Force - 11
DLA – CC

Preparing activity:
DLA-CC

(Project 5961-2007-064)

Review activities:
Army – AR, MR, SM
Navy – AS, MC, SH
Air Force - 19

* NOTE: The activities listed above were interested in this document as of the date of this document. Since organizations and responsibilities can change, you should verify the currency of the information above using the ASSIST Online database at <http://assist.daps.dla.mil>.